SQJ414EP

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Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	30
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0120
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0170
I _D (A)	30
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

N-Channel MOSFET

D

S



COMPLIANT HALOGEN

ABSOLUTE MAXIMUM RATINGS (T _C =	= 25 °C, unles	ss otherwise notec	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	30	v
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current	$T_C = 25 \ ^\circ C \ ^a$	² C ^a 30		
Continuous drain current	T _C = 125 °C	Ι _D	25	
Continuous source current (diode conduction) ^a	ا _S	30	А	
Pulsed drain current ^b	I _{DM}	90		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	22	
Single pulse avalanche energy	L = 0.1 mm	E _{AS}	24.2	mJ
Maximum power dissipation ^b	T _C = 25 °C	PD	45	w
Maximum power dissipation -	T _C = 125 °C	гD	15	vv
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^{d, e}			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	70	°C/W
Junction-to-case (drain)		R _{thJC}	3.3	C/W

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static		•		•				
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		30	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2.0	2.5	v	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 30 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250		
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	15	-	-	А	
		$V_{GS} = 10 \text{ V}$	I _D = 4.5 A	-	0.0098	0.0120		
Drain aquraa an atata ragistanga a	D	$V_{GS} = 4.5 V$	I _D = 3 A	-	0.0139	0.0170	Ω	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 4.5 A, T _J = 125 °C	-	-	0.0188		
		$V_{GS} = 10 \text{ V}$	I _D = 4.5 A, T _J = 175 °C	-	-	0.0227		
Forward transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 4 A	-	31	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	850	1110		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 15 V, f = 1 MHz	-	167	220	pF	
Reverse transfer capacitance	C _{rss}			-	60	80		
Total gate charge ^c	Qg		V _{DS} = 15 V, I _D = 5 A	-	15	25	nC	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V		-	3	-		
Gate-drain charge ^c	Q _{gd}			-	3	-		
Gate resistance	Rg	f = 1 MHz		0.7	1.5	2.3	Ω	
Turn-on delay time ^c	t _{d(on)}			-	11	20		
Rise time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD} = 15 \; V, \; R_L = 3.8 \; \Omega \\ I_D \cong 4 \; A, \; V_GEN = 10 \; V, \; R_g = 1 \; \Omega \end{array}$		-	5	10	- ns	
Turn-off delay time ^c	t _{d(off)}			-	21	40		
Fall time ^c	t _f			-	5	10		
Source-Drain Diode Ratings and Charac	cteristics ^b	•			•			
Pulsed current ^a	I _{SM}			-	-	90	Α	
Forward voltage	V _{SD}	$I_{\rm F} = 4 {\rm A}, {\rm V}_{\rm GS} = 0$		-	0.79	1.2	V	
Body diode reverse recovery time	t _{rr}			-	22	50	ns	
Body diode reverse recovery charge	Q _{rr}	- I _F = 3 A, di/dt = 100 A/μs		-	18	40	nC	
Reverse recovery fall time	ta			-	14	-		
Reverse recovery rise time	t _b			-	8	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.5	-	Α	

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

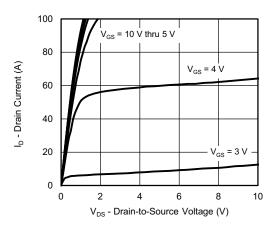
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

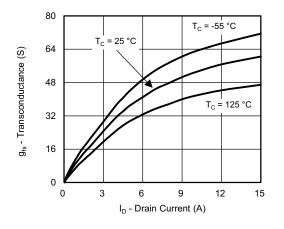
2



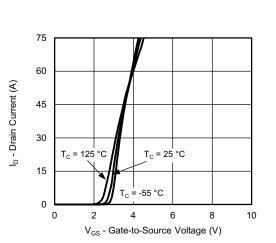
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



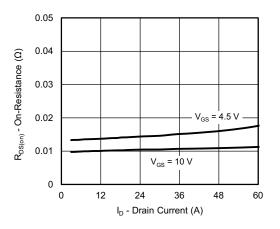
Output Characteristics



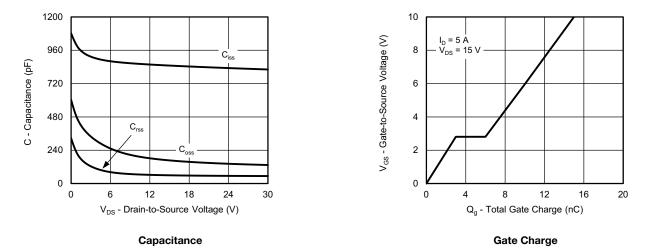
Transconductance



Transfer Characteristics



On-Resistance vs. Drain Current



S17-0520-Rev. A, 10-Apr-17

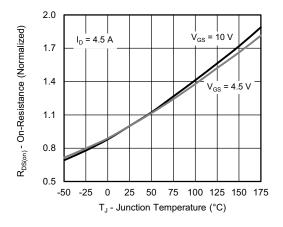
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Document Number: 75498

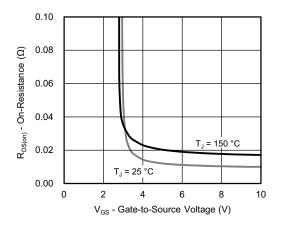
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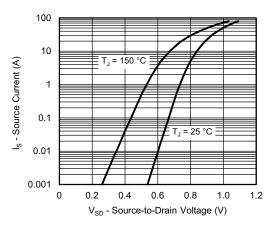
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



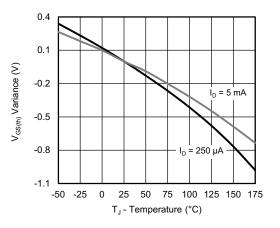
On-Resistance vs. Junction Temperature

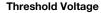


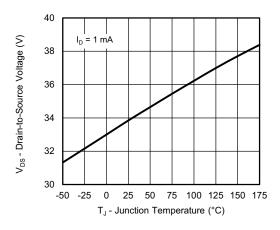
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







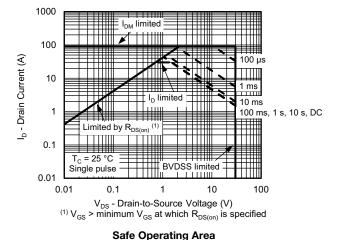
Drain Source Breakdown vs. Junction Temperature

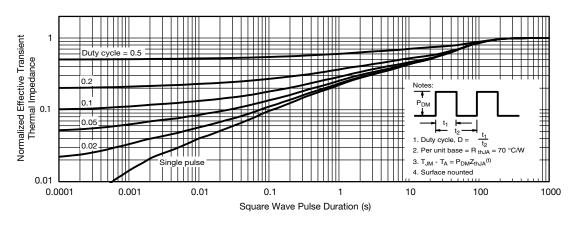
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



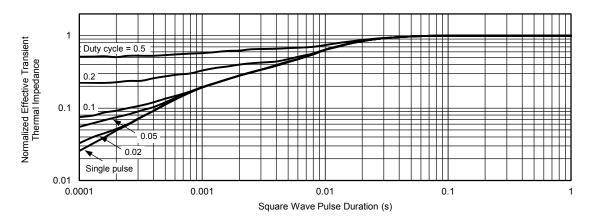


Normalized Thermal Transient Impedance, Junction-to-Ambient



Document Number: 75498

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

S17-0520-Rev. A, 10-Apr-17

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75498.









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Package Information



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DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51			0.020		
W	0.23			0.009			
W1	0.41			0.016			
W2	2.82			0.111			
W3		2.96			0.117		
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



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